MSKSEMI















ESD

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Broduct data sheet

DTA123JE-MS HF



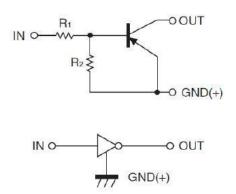


SOT-523

FEATURES:

- Built-in resistors enable the configuration of a inverter circuit without connecting external input resistors.
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.
- **RoHS Compliant**
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

ELECTRICAL SYMBOL:





Electrical Characteristics ($T_A = 25^{\circ}C$ unless otherwise noted)

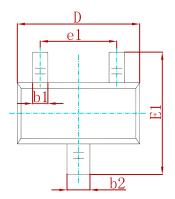
Parameter	O. wash a l	Took Condition	Limits			11
	Symbol	Test Condition	Min	Тур	Max	Unit
Input Voltage	V _{I(off)}	V _{CC} = -5V, I _O = -100uA	-0.5			V
	V _{I(on)}	V _O = -0.3V, I _O =-5mA			-1.1	V
Output Voltage	V _{O(on)}	I _O / I _I = -5mA/-0.25mA		-0.1	-0.3	V
Input Current	l ₁	V _I = -5V			-3.6	mA
Output Current	I _{O(off)}	V _{CC} = -50V, V _I = 0V			-0.5	uA
DC Current Gain	Gı	V _O = -5V, I _O = -10mA	80			
Input Resistance	R ₁		1.54	2.2	2.86	ΚΩ
Resistance Ratio	R ₂ /R ₁		17	21	26	
Transition Frequency	f⊤	$V_0 = -10V, I_0 = -5mA$ f=100MHz		250		MHz

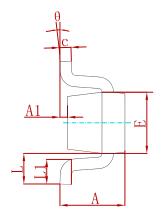
Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

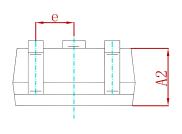
Symbol	Parameter	Value	Units
V _{cc}	Supply Voltage	-50	V
V _{IN}	Input Voltage	-12 ~ +5	V
Io	Output Current	-100	mA
I _{CM}	Peak Collector Current	-100	mA
P _D	Power Dissipation	150	mW
TJ	Junction to Ambient	150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C



PACKAGE MECHANICAL DATA

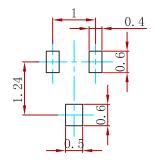






Comple ed	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016 REF.		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
DTA123JE-MS	SOT-523	3000



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NSVMUN5135DW1T1G NSVMUN2237T1G NSVDTC143ZM3T5G SMUN5335DW1T2G SMUN5216DW1T1G NSVMUN5316DW1T1G

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